Everspin and GLOBALFOUNDRIES Partner to Supply Fully Processed 300mm CMOS Wafers with Everspin's ST-MRAM Technology

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Partnership with leading foundry will support Everspin's ST-MRAM market growth starting with 40nm and 28nm technology

Chandler, AZ, Oct 27, 2014 —Everspin Technologies, Inc., the world's leading developer and manufacturer of discrete and embedded MRAM, today announced that the company has partnered with GLOBALFOUNDRIES to build fully processed 300mm wafers with Everspin's magnetic tunnel junction (MTJ) Spin-Torque Magnetoresistive Random-Access Memory (ST-MRAM) technology, starting with GF 40 nanometer and 28 nanometer Low Power CMOS platforms. This relationship forms the core of Everspin's long-term strategy to proliferate ST-MRAM into the marketplace by offering designers of high performance storage systems a fast, non-volatile memory solution featuring low latency and increased reliability.

GF has invested in advanced ST-MRAM CMOS processing equipment to deliver the fully processed CMOS and MRAM wafers beginning with GF's 40 nanometer technology node. GF has also invested an undisclosed amount in Everspin.

"Everspin's experience in shipping over 40 million MRAM products to the market, as well as designing and launching the first commercially-available ST-MRAM, together with our manufacturing capability will establish the industry's first 300mm ST-MRAM technology" said Gregg Bartlett, senior vice president of product management at GF. "Our partnership with Everspin will help drive ST-MRAM adoption and feed the rapidly growing MRAM market."

"GF is a pioneer in delivering value-added and fully-integrated memory solutions to a multitude of markets and applications," said Phill LoPresti, President and CEO at Everspin. "Our partnership with a world-class foundry is a fundamental piece of our long-term strategy to deliver ST-MRAM on 300mm, accelerate availability of our perpendicular MTJ ST-MRAM bit cell, fast-track ST-MRAM production in advanced CMOS technology nodes, secure high volume capacity for our customers, and scale ST-MRAM towards Gigabit densities to further expand the market and application uses of Everspin ST-MRAM products."

About Everspin Technologies

Everspin Technologies is the worldwide leader in designing, manufacturing, and commercially shipping discrete and embedded Magnetoresistive RAM (MRAM) and Spin-Torque MRAM (ST-MRAM) into markets and applications where data persistence and integrity, low latency, and security are paramount. With over 40 Million MRAM and ST-MRAM products deployed in data center, cloud storage, energy, industrial, automotive, and transportation markets, Everspin has built the strongest and fastest growing foundation of MRAM users in the world. With an intellectual property portfolio of more than 500 active patents and applications, Everspin leads the market in development of both in-plane and perpendicular magnetic tunnel junction (MTJ) ST-MRAM bit cells. Everspin has established high-quality manufacturing worldwide, along with enabling a full turn-key 300mm high-volume foundry partner for advanced technology nodes including 40nm, 28nm and beyond. In addition to launching discrete memory solutions with new densities and advanced interfaces, including the world's first commercialization and volume shipments of ST-MRAM, Everspin is delivering on the company's strategy to proliferate MRAM and ST-MRAM as mainstream embedded memories for use in MCUs, GPUs, DSPs, Application Processors, and ASICs, earning Everspin its description as "The MRAM Company". www.everspin.com

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Everspin Contact:

Michael Schoolnik
Story Public Relations
415-674-3816
michael@storypr.com